

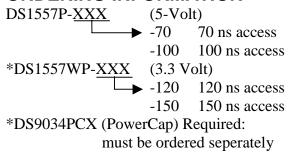
DS1557 4MEG NV Y2KC Timekeeping RAM

www.dalsemi.com

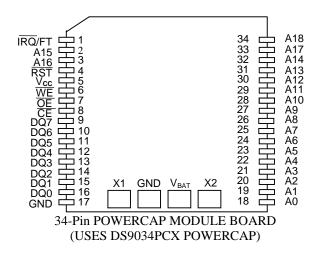
FEATURES

- Integrated NV SRAM, real time clock, crystal, power-fail control circuit and lithium energy source
- Clock registers are accessed identically to the static RAM; these registers are resident in the 16 top RAM locations
- Century byte register; i.e., Y2K complaint
- Totally nonvolatile with over 10 years of operation in the absence of power
- Precision power-on reset
- Programmable watchdog timer and RTC alarm
- BCD coded year, month, date, day, hours, minutes, and seconds with automatic leap year compensation valid up to the year 2100
- Battery voltage level indicator flag
- Power-fail write protection allows for ±10%
 V_{CC} power supply tolerance
- Lithium energy source is electrically disconnected to retain freshness until power is applied for the first time

ORDERING INFORMATION



PIN ASSIGNMENT



PIN DESCRIPTION

FIN DESCRIP II	ON
A0-A14	- Address Input
DQ0-DQ7	- Data Input/Outputs
IRQ \FT	- Interrupt, Frequency Test
	Output (Open Drain)
RST	- Power-On Reset Output
	(Open Drain)
CE	- Chip Enable
ŌE	- Output Enable
$\overline{ ext{WE}}$	- Write Enable
V_{CC}	- Power Supply Input
GND	- Ground
NC	- No Connection
X1, X2	- Crystal Connection
V_{BAT}	- Battery Connection

DESCRIPTION

The DS1557 is a full function, year 2000-compliant (Y2KC), real-time clock/calendar (RTC) with a RTC alarm, watchdog timer, power-on reset, battery monitor, and 512k x 8 non-volatile static RAM. User access to all registers within the DS1557 is accomplished with a bytewide interface as shown in Figure 1. The RTC Registers contain century, year, month, date, day, hours, minutes, and seconds data in 24-hour BCD format. Corrections for day of month and leap year are made automatically.

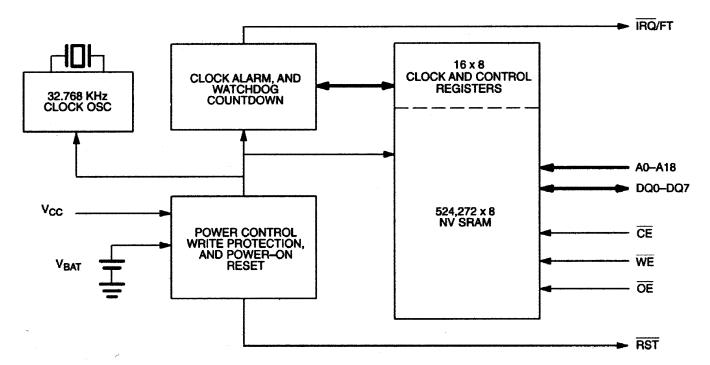
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The RTC Registers are double-buffered into an internal and external set. The user has direct access to the external set. Clock/calendar updates to the external set of registers can be disabled and enabled to allow the user to access static data. Assuming the internal oscillator is turned on, the internal set of registers are continuously updated; this occurs regardless of external registers settings to guarantee that accurate RTC information is always maintained.

The \overline{IRQ}/FT interrupt (\overline{IRQ}/FT) and reset (\overline{RST}) outputs which can be used to control CPU activity. The \overline{IRQ}/FT interrupt output can be used to generate an external interrupt when the RTC Register values match user programmed alarm values. The interrupt is always available while the device is powered from the system supply and can be programmed to occur when in the battery backed state to serve as a system wake-up. Either the \overline{IRQ}/FT or \overline{RST} outputs can also be used as a CPU watchdog timer, CPU activity is monitored and an interrupt or reset output will be activated if the correct activity is not detected within programmed limits. The DS1557 power-on reset can be used to detect a system power down or failure and hold the CPU in a safe reset state until normal power returns and stabilizes; the \overline{RST} output is used for this function.

The DS1557 also contains its own power-fail circuitry which automatically deselects the device when the V_{CC} supply enters an out of tolerance condition. This feature provides a high degree of data security during unpredictable system operation brought on by low V_{CC} levels.

DS1557 BLOCK DIAGRAM Figure 1



DS1557 OPERATING MODES Table 1

V_{CC}	CE	ŌE	WE	DQ0-DQ7	MODE	POWER
	V_{IH}	X	X	HIGH-Z	DESELECT	STANDBY
$V \sim V$	$V_{\rm IL}$	X	$V_{\rm IL}$	$\mathrm{D_{IN}}$	WRITE	ACTIVE
$V_{\rm CC} > V_{\rm PF}$	$V_{\rm IL}$	$V_{\rm IL}$	V_{IH}	D_{OUT}	READ	ACTIVE
	$V_{\rm IL}$	V_{IH}	V_{IH}	HIGH-Z	READ	ACTIVE
$V_{SO} < V_{CC} < V_{PF}$	X	X	X	HIGH-Z	DESELECT	CMOS STANDBY
$V_{\rm CC} < V_{\rm SO}$	X	X	X	HIGH-Z	DATA	BATTERY
					RETENTION	CURRENT

DATA READ MODE

The DS1557 is in the read mode whenever \overline{CE} (chip enable) is low and \overline{WE} (write enable) is high. The device architecture allows ripple-through access to any valid address location. Valid data will be available at the DQ pins within t_{AA} after the last address input is stable, providing that \overline{CE} and \overline{OE} access times are satisfied. If \overline{CE} or \overline{OE} access times are not met, valid data will be available at the latter of chip enable access (t_{CEA}) or at output enable access time (t_{OEA}). The state of the data input/output pins (DQ) is controlled by \overline{CE} and \overline{OE} . If the outputs are activated before t_{AA} , the data lines are driven to an intermediate state until t_{AA} . If the address inputs are changed while \overline{CE} and \overline{OE} remain valid, output data will remain valid for output data hold time (t_{OH}) but will then go indeterminate until the next address access.

DATA WRITE MODE

The DS1557 is in the write mode whenever \overline{WE} and \overline{CE} are in their active state. The start of a write is referenced to the latter occurring transition of \overline{WE} or \overline{CE} . The addresses must be held valid throughout the cycle. \overline{CE} and \overline{WE} must return inactive for a minimum of t_{WR} prior to the initiation of a subsequent read or write cycle. Data in must be valid t_{DS} prior to the end of the write and remain valid for t_{DH} afterward. In a typical application, the \overline{OE} signal will be high during a write cycle. However, \overline{OE} can be active provided that care is taken with the data bus to avoid bus contention. If \overline{OE} is low prior to \overline{WE} transitioning low, the data bus can become active with read data defined by the address inputs. A low transition on \overline{WE} will then disable the outputs t_{WEZ} after \overline{WE} goes active.

DATA RETENTION MODE

The 5-volt device is fully accessible and data can be written and read only when V_{CC} is greater than V_{PF} . However, when V_{CC} is below the power-fail point V_{PF} (point at which write protection occurs) the internal clock registers and SRAM are blocked from any access. When V_{CC} falls below the battery switch point V_{SO} (battery supply level), device power is switched from the V_{CC} pin to the internal backup lithium battery. RTC operation and SRAM data are maintained from the battery until V_{CC} is returned to nominal levels.

The 3.3-volt device is fully accessible and data can be written and read only when V_{CC} is greater than V_{PF} . When V_{CC} falls below V_{PF} , access to the device is inhibited. If V_{PF} is less than V_{BAT} , the device power is switched from V_{CC} to the internal backup lithium battery when V_{CC} drops below V_{PF} . If V_{PF} is greater than V_{BAT} , the device power is switched from V_{CC} to the internal backup lithium battery when V_{CC} drops below V_{BAT} . RTC operation and SRAM data are maintained from the battery until V_{CC} is returned to nominal levels.

All control, data, and address signals must be powered down when V_{CC} is powered down.

BATTERY LONGEVITY

The DS1557 has a lithium power source that is designed to provide energy for the clock activity, and clock and RAM data retention when the V_{CC} supply is not present. The capability of this internal power supply is sufficient to power the DS1557 continuously for the life of the equipment in which it is installed. For specification purposes, the life expectancy is 10 years at 25°C with the internal clock oscillator running in the absence of V_{CC} .

INTERNAL BATTERY MONITOR

The DS15573 constantly monitors the battery voltage of the internal batter. The Battery Low Flag (BLF) bit of the Flags Register (B4 of 7FFF0h) is not writable and should always be a 0 when read. If a 1 is ever present, an exhausted lithium energy source is indicated and both the contents of the RTC and RAM are questionable.

POWER-ON RESET

A temperature compensated comparator circuit monitors the level of V_{CC} . When V_{CC} falls to the power fail trip point, the \overline{RST} signal (open drain) is pulled low. When V_{CC} returns to nominal levels, the \overline{RST} signal continues to be pulled low for a period of 40 ms to 200 ms. The power-on reset function is independent of the RTC oscillator and thus is operational whether or not the oscillator is enabled.

CLOCK OPERATIONS

Table 2 and the following paragraphs describe the operation of RTC, alarm, and watchdog functions.

DS1557 REGISTER MAP Table 2

	DATA									
ADDRESS	B ₇	B ₆	B ₅	B ₄	B ₃	$\mathbf{B_2}$	\mathbf{B}_{1}	\mathbf{B}_{0}	FUNCTION/RAN	GE
7FFFh		10	Year			YEA	R		YEAR	00-99
7FFEh	X	X	X	10 M		MONT	ΤΗ		MONTH	01-12
7FFDh	X	X	10 I	Date		DAT	Е		DATE	01-31
7FFCh	X	FT	X	X	X		DAY		DAY	01-07
7FFBh	X	X	10 H	OUR		HOU	R		HOUR	00-23
7FFAh	X	10) MINUTI	ES	MINUTES			MINUTES	00-59	
7FF9h	OSC	10) SECONDS			SECON	IDS		SECONDS	00-59
7FF8h	W	R	10 CEN	NTURY		CENTU	RY		CONTROL	00-39
7FF7h	WDS	BMB4	BMB3	BMB2	BMB1	BMB0	RB1	RB0	WATCHDOG	
7FF6h	AE	Y	ABE	Y	Y	Y	Y	Y	INTERRUPTS	
7FF5h	AM4	Y	10 D	ATE		DAT	E		ALARM DATE	01-31
7FF4h	AM3	Y	10 HC	OURS		HOUF	RS		ALARM HOURS	00-23
7FF3h	AM2	10) MINUTI	ES	MINUTES				ALARM MINUTES	00-59
7FF2h	AM1	10) SECONI	OS	SECONDS				ALARM SECONDS	00-59
7FF1h	Y	Y	Y	Y	Y	Y	Y	Y	UNUSED	
7FF0h	WF	AF	0	BLF	0	0	0	0	FLAGS	

X = Unused, read/writable under Write and Read bit control

FT = Frequency Test bit

OSC = Oscillator start/stop bit

W = Write bit

R = Read bit

WDS = Watchdog Steering bit

BMB0-BMB4 = Watchdog Multiplier bits

RB0-RB1 = Watchdog Resolution bits

AE = Alarm Flag Enable

Y = Unused, read/writable without Write and Read

bit control

ABE = Alarm in battery Back-up mode enable

AM1-AM4 = Alarm Mask bits

WF = Watchdog Flag

AF = Alarm Flag

0 = 0 and are read only

BLF = Battery Low Flag

CLOCK OSCILLATOR CONTROL

The Clock oscillator may be stopped at any time. To increase the shelf life of the backup lithium battery source, the oscillator can be turned off to minimize current drain from the battery. The \overline{OSC} bit is the MSB of the Seconds Register (B7 of 7FF9h). Setting it to a 1 stops the oscillator, setting to a 0 starts the oscillator. The DS1557 is shipped from Dallas Semiconductor with the clock oscillator turned off, \overline{OSC} bit set to a 1.

READING THE CLOCK

When reading the RTC data, it is recommended to halt updates to the external set of double-buffered RTC Registers. This puts the external registers into a static state allowing data to be read without register values changing during the read process. Normal updates to the internal registers continue while in this state. External updates are halted when a 1 is written into the read bit, B6 of the Control Register (7FF8h). As long as a 1 remains in the Control Register read bit, updating is halted. After a halt is issued, the registers reflect the RTC count (day, date, and time) that was current at the moment the halt command was issued. Normal updates to the external set of registers will resume within 1 second after the read bit is set to a 0.

SETTING THE CLOCK

The 8th bit, B7 of the Control Register is the write bit. Setting the write bit to a 1, like the read bit, halts updates to the DS1557 (7FF8h-7FFFh) registers. After setting the write bit to a 1, RTC Registers can be loaded with the desired RTC count (day, date, and time) in 24-hour BCD format. Setting the write bit to a 0 then transfers the values written to the internal RTC Registers and allows normal operation to resume.

CLOCK ACCURACY

The DS1557 and DS9034PCX are each individually tested for accuracy. Once mounted together, the module is guaranteed to keep time accuracy to within ±1.53 minutes per month (35 ppm) at 25°C. The DS1557 does not require additional calibration and, in most applications, temperature deviations will have a negligible effect on accuracy. For this reason, methods of field clock calibration are not available and not necessary. Attempts to calibrate the RTC that may be used with similar device types (M48T5x family) will not have any effect even though the DS1557 appears to accept calibration data.

FREQUENCY TEST MODE

The DS1557 frequency test mode uses the open drain \overline{IRQ}/FT output. With the oscillator running, the \overline{IRQ}/FT output will toggle at 512 Hz when the FT bit is a 1, the Alarm Flag Enable bit (AE) is a 0, and the Watchdog Steering bit (WDS) is a 1 or the Watchdog Register is reset (Register 7FF7h = 00h). The \overline{IRQ}/FT output and the frequency test mode can be used as a measure of the actual frequency of the 32.768 kHz RTC oscillator. The \overline{IRQ}/FT pin is an open drain output which requires a pullup resistor for proper operation. The FT bit is cleared to a 0 on power-up.

USING THE CLOCK ALARM

The alarm settings and control for the DS1557 reside within Registers 7FF2h-7FF5h. Register 7FF6h contains two alarm enable bits: Alarm Enable (AE) and Alarm in Backup Enable (ABE). The AE and ABE bits must be set as described below for the \overline{IRQ}/FT output to be activated for a matched alarm condition.

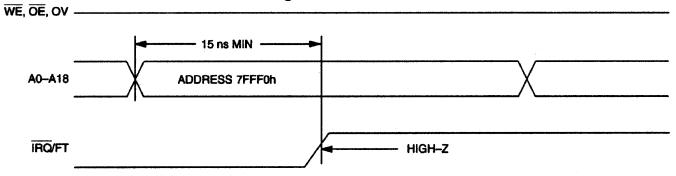
The alarm can be programmed to activate on a specific day of the month or repeat every day, hour, minute, or second. It can also be programmed to go off while the DS1557 is in the battery backed state of operation to serve as a system wake-up. Alarm mask bits AM1-AM4 control the alarm mode. Table 3 shows the possible settings. Configurations not listed in the table default to the once per second mode to notify the user of an incorrect alarm setting.

ALARM MASK BITS Table 3

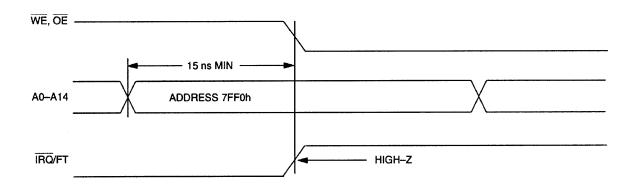
AM4	AM3	AM2	AM1	ALARM RATE			
1	1	1	1	Once per second			
1	1	1	0	When seconds match			
1	1	0	0	When minutes and seconds match			
1	0	0	0	When hours, minutes, and seconds match			
0	0	0	0	When date, hours, minutes, and seconds match			

When the RTC Register values match Alarm Register settings, the Alarm Flag bit (AF) is set to a 1. If Alarm Flag Enable (AE) is also set to a 1, the alarm condition activates the \overline{IRQ}/FT pin. The \overline{IRQ}/FT signal is cleared by a read or write to the Flags Register (Address 7FF0h) as shown in Figure 2 and 3. The \overline{IRQ}/FT signal may be cleared by having the address stable for as short as 15 ns and either \overline{CE} or \overline{WE} active, but is not guaranteed to be cleared unless t_{RC} is fulfilled. The alarm flag is also cleared by a read or write to the Flags Register but the flag will not change states until the end of the read/write cycle and the \overline{IRQ}/FT signal has been cleared.

CLEARING IRQ WAVEFORMS Figure 2

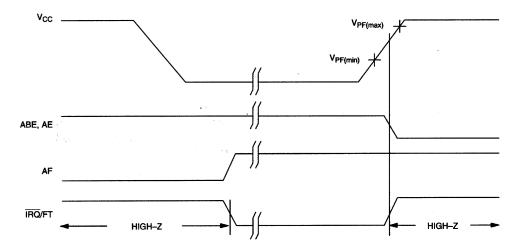


CLEARING IRQ WAVEFORMS Figure 3



The IRQ/FT pin can also be activated in the battery backed mode. The IRQ/FT will go low if an alarm occurs and both ABE and AE are set. The ABE and AE bits are cleared during the power-up transition, however an alarm generated during power-up will set AF. Therefore the AF bit can be read after system power-up to determine if an alarm was generated during the power-up sequence. Figure 4 illustrates alarm timing during the battery back-up mode and power-up states.

BACK-UP MODE ALARM WAVEFORMS Figure 4



USING THE WATCHDOG TIMER

The watchdog timer can be used to detect an out-of-control processor. The user programs the watchdog timer by setting the desired amount of time-out into the 8-bit Watchdog Register (Address 7FF7h). The five Watchdog Register bits BMB4-BMB0 store a binary multiplier and the two lower order bits RB1-RB0 select the resolution, where 00=1/16 second, 01=1/4 second, 10=1 second, and 11=4 seconds. The watchdog time-out value is then determined by the multiplication of the 5-bit multiplier value with the 2-bit resolution value. (For example: writing 00001110 in the Watchdog Register = 3 X 1 second or 3 seconds.) If the processor does not reset the timer within the specified period, the Watchdog Flag (WF) is set and a processor interrupt is generated and stays active until either the Watchdog Flag (WF) is read or the Watchdog Register (7FF7) is read or written.

The most significant bit of the Watchdog Register is the Watchdog Steering Bit (WDS). When set to a 0, the watchdog will activate the \overline{IRQ} /FT output when the watchdog times out.

When WDS is set to a 1, the watchdog will output a negative pulse on the $\overline{\text{RST}}$ output for a duration of 40 ms to 200 ms. The Watchdog Register (7FF7) and the FT bit will reset to a 0 at the end of a watchdog time-out when the WDS bit is set to a 1.

The watchdog timer resets when the processor performs a read or write of the Watchdog Register. The time-out period then starts over. The watchdog timer is disabled by writing a value of 00h to the Watchdog Register. The watchdog function is automatically disabled upon power-up and the Watchdog Register is cleared. If the watchdog function is set to output to the \overline{IRQ}/FT output and the frequency test function is activated, the watchdog function prevails and the frequency test function is denied.

POWER-ON DEFAULT STATES

Upon application of power to the device, the following register bits are set to a 0: WDS=0, BMB0-BMB4=0, RB0-RB1=0, AE=0, ABE=0.

ABSOLUTE MAXIMUM RATINGS*

Voltage on Any Pin Relative to Ground -5.0V to +6.0V Operating Temperature 0°C to 70°C Storage Temperature -55°C to +125°C

Soldering Temperature 260°C for 10 seconds (See Note 8)

RECOMMENDED DC OPERATING CONDITIONS

(0°C to 70°C)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Logic 1 Voltage All Inputs						
$V_{CC} = 5V \pm 10\%$	$V_{ m IH}$	2.2		$V_{CC} + 0.3V$	V	1
$V_{CC} = 3.3V \pm 10\%$	V_{IH}	2.0		V _{CC} +0.3V	V	1
Logic 0 Voltage All Inputs						
$V_{CC} = 5V \pm 10\%$	V_{IL}	-0.3		0.8		1
$V_{CC} = 3.3V \pm 10\%$	$V_{\rm IL}$	-0.3		0.6		1

DC ELECTRICAL CHARACTERISTICS

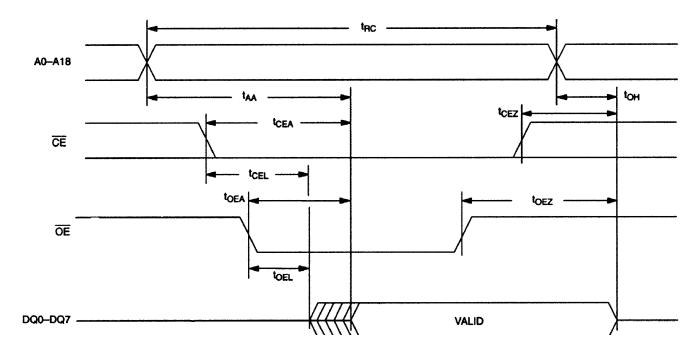
 $(0^{\circ}\text{C to } 70^{\circ}\text{C}; V_{\text{CC}} = 5.0\text{V} \pm 10\%)$

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Active Supply Current	I_{CC}		X	90	mA	2, 3
TTL Standby Current ($\overline{CE} = V_{IH}$)	I_{CC1}		X	6	mA	2, 3
CMOS Standby Current	I_{CC2}		X	4	mA	2, 3
$(\overline{CE} \ge V_{CC} - 0.2V)$						
Input Leakage Current (any input)	I_{IL}	-1		+1	μΑ	
Output Leakage Current (any	I_{OL}	-1		+1	μΑ	
output)						
Output Logic 1 Voltage	V_{OH}	2.4			V	1
$(I_{OUT} = -1.0 \text{ mA})$						
Output Logic 0 Voltage						
$(I_{OUT} = 2.1 \text{ mA}, DQ0-7 \text{ Outputs})$	V_{OL1}			0.4	V	1
$(I_{OUT} = 10.0 \text{ mA}, \overline{IRQ}/FT \text{ and}$	V_{OL2}			0.4	V	1, 5
RST outputs)						
Write Protection Voltage	V_{PF}	4.25	4.37	4.50	V	1
Battery Switch Over Voltage	V_{SO}		V_{BAT}		V	1, 4

^{*} This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operation sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods of time may affect reliability.

OC ELECTRICAL CHARACTERISTICS			(0°C to	$(0^{\circ}\text{C to }70^{\circ}\text{C}; V_{\text{CC}} = 3.3\text{V} \pm 10\%)$				
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES		
Active Supply Current	I_{CC}		X	30	mA	2, 3		
TTL Standby Current ($\overline{\text{CE}} = V_{\text{IH}}$)	I_{CC1}		X	3	mA	2, 3		
CMOS Standby Current $(\overline{CE} \ge V_{CC} - 0.2V)$	I_{CC2}		X	2	mA	2, 3		
Input Leakage Current (any input)	I_{IL}	-1		+1	μΑ			
Output Leakage Current (any output)	I_{OL}	-1		+1	μA			
Output Logic 1 Voltage (I _{OUT} = -1.0 mA)	V_{OH}	2.4			V	1		
Output Logic 0 Voltage								
$(I_{OUT} = 2.1 \text{ mA}, DQ0-7 \text{ Outputs})$	V_{OL1}			0.4	V	1		
$(I_{OUT} = 10.0 \text{ mA}, \overline{IRQ}/FT \text{ and } \overline{RST} \text{ Outputs})$	$ m V_{OL2}$			0.4	V	1, 5		
Write Protection Voltage	V_{PF}	2.80	2.88	2.97	V	1		
Battery Switch Over Voltage	V_{SO}		V_{BAT} or V_{PF}		V	1, 4		

READ CYCLE TIMING DIAGRAM Figure 5



READ CYCLE, AC CHARACTERISTICS

 $(0^{\circ}\text{C to } 70^{\circ}\text{C}; V_{\text{CC}} = 5.0\text{V} \pm 10\%)$

		70 ns access		100 ns access			
PARAMETER	SYMBOL	MIN	MAX	MIN	MAX	UNITS	NOTES
Read Cycle Time	t_{RC}	70		100		ns	
Address Access Time	t_{AA}		70		100	ns	
CE to DQ Low-Z	$t_{ m CEL}$	5		5		ns	
CE Access Time	t_{CEA}		70		100	ns	
CE Data Off time	t_{CEZ}		25		35	ns	
OE to DQ Low-Z	t _{OEL}	5		5		ns	
OE Access Time	t _{OEA}		35		55	ns	
OE Data Off Time	t _{OEZ}		25		35	ns	
Output Hold from Address	t _{OH}	5		5		ns	

READ CYCLE, AC CHARACTERISTICS

 $(0^{\circ}\text{C to }70^{\circ}\text{C}; V_{\text{CC}} = 3.3\text{V} \pm 10\%)$

		120 ns	access	ss 150 ns access			
PARAMETER	SYMBOL	MIN	MAX	MIN	MAX	UNITS	NOTES
Read Cycle Time	t_{RC}	120		150		ns	
Address Access Time	t_{AA}		120		150	ns	
CE to DQ Low-Z	t _{CEL}	5		5		ns	
CE Access Time	t_{CEA}		120		150	ns	
CE Data Off time	t_{CEZ}		40		50	ns	
OE to DQ Low-Z	$t_{ m OEL}$	5		5		ns	
OE Access Time	t_{OEA}		100		130	ns	
OE Data Off Time	t _{OEZ}		35		35	ns	
Output Hold from Address	t_{OH}	5		5		ns	

WRITE CYCLE, AC CHARACTERISTICS

 $(0^{\circ}\text{C to }70^{\circ}\text{C}; \text{V}_{\text{CC}} = 5.0\text{V} \pm 10\%)$

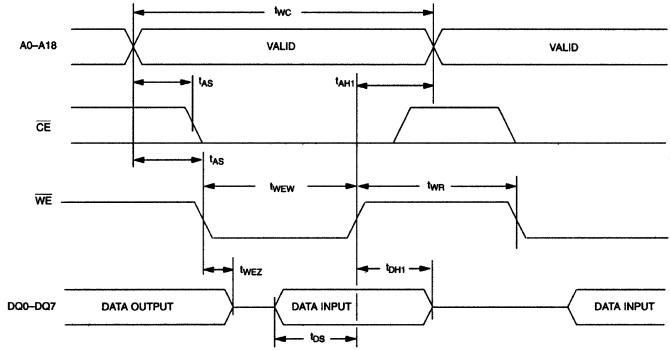
		70 ns	access	100 ns	access		
PARAMETER	SYMBOL	MIN	MAX	MIN	MAX	UNITS	NOTES
Write Cycle Time	t_{WC}	70		100		ns	
Address Access Time	t_{AS}	0		0		ns	
WE Pulse Width	t_{WEW}	50		70		ns	
CE Pulse Width	t_{CEW}	60		75		ns	
Data Setup Time	t_{DS}	30		40		ns	
Data Hold time	t _{DH1}	0		0		ns	9
Data Hold time	t _{DH2}	X		X		ns	10
Address Hold Time	t _{AH1}	5		5		ns	9
Address Hold Time	t _{AH2}	X		X		ns	10
WE Data Off Time	$t_{ m WEZ}$		25		35	ns	
Write Recovery Time	t _{WR}	5		5		ns	

WRITE CYCLE, AC CHARACTERISTICS

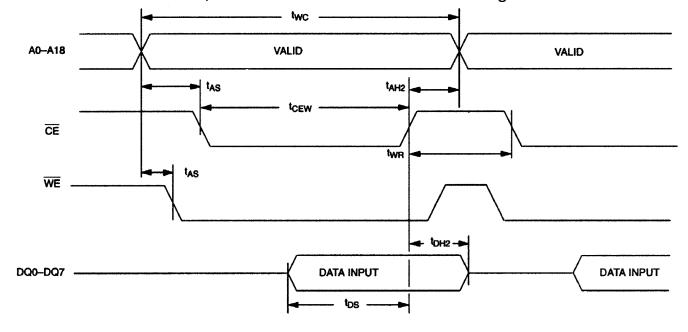
 $(0^{\circ}\text{C to } 70^{\circ}\text{C}; V_{\text{CC}} = 3.3\text{V} \pm 10\%)$

		120 ns	access	150 ns	access		
PARAMETER	SYMBOL	MIN	MAX	MIN	MAX	UNITS	NOTES
Write Cycle Time	t_{WC}	120		150		ns	
Address Setup Time	t_{AS}	0		0		ns	
WE Pulse Width	$t_{ m WEW}$	100		130		ns	
CE Pulse Width	t_{CEW}	110		140		ns	
Data Setup Time	$t_{ m DS}$	80		90		ns	
Data Hold Time	t _{DH1}	0		0		ns	9
Data Hold Time	t_{DH2}	X		X		ns	10
Address Hold Time	t _{AH1}	0		0		ns	9
Address Hold Time	t _{AH2}	X		X		ns	10
WE Data Off Time	$t_{ m WEZ}$		40		50	ns	
Write Recovery Time	t_{WR}	10		10		ns	

WRITE CYCLE TIMING, WRITE ENABLE CONTROLLED Figure 6



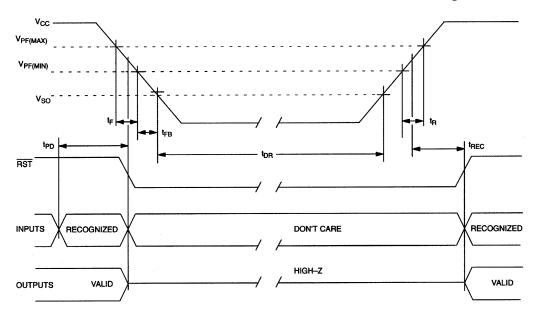
WRITE CYCLE TIMING, CHIP ENABLE CONTROLLED Figure 7



POWER-UP/DOWN CHARACTERISTICS	$(0^{\circ}\text{C to }70^{\circ}\text{C}; V_{\text{CC}} = 5.0\text{V} \pm 10\%)$
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PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
CE or WE at V _{IH} , Before Power-Down	t _{PD}	0			μs	
V_{CC} Fall Time: $V_{PF(MAX)}$ to $V_{PF(Min)}$	t_{F}	300			μs	
V_{CC} Fall Time: $V_{PF(MIN)}$ to V_{SO}	t_{FB}	10			μs	
V_{CC} Rise Time: $V_{PF(MIN)}$ to $V_{PF(MAX)}$	t _R	0			μs	
V _{PF} to RST High	t_{REC}	40		200	ms	
Expected Data Retention Time (Oscillator On)	t _{DR}	10			years	6

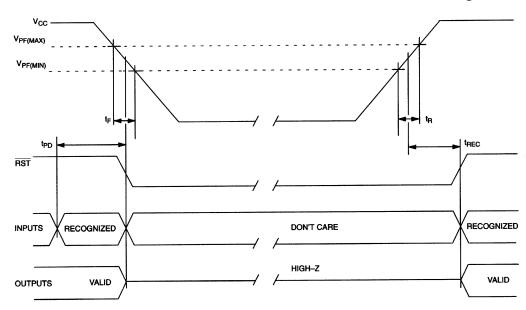
POWER-UP/DOWN WAVEFORM TIMING 5-VOLT DEVICE Figure 8



POWER-UP/DOWN CHARACTERISTICS	$(0^{\circ}\text{C to }70^{\circ}\text{C}; V_{CC} = 3.3\text{V} \pm 10\%)$
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			(5 5 15 1 5 6)			
PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
$\overline{\text{CE}}$ or $\overline{\text{WE}}$ at V_{IH} , Before Power-Down	t _{PD}	0			μs	
V_{CC} Fall Time: $V_{PF(MAX)}$ to $V_{PF(Min)}$	$t_{ m F}$	300			μs	
V_{CC} Rise Time: $V_{PF(MIN)}$ to $V_{PF(MAX)}$	t_R	0			μs	
V _{PF} to RST High	t_{REC}	40		200	ms	
Expected Data Retention Time (Oscillator On)	t_{DR}	10			years	6

POWER-UP/DOWN WAVEFORM TIMING 3.3-VOLT DEVICE Figure 9



CAPACITANCE $(T_A = 25^{\circ}C)$

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	NOTES
Capacitance on all input pins	C_{IN}			7	pF	1
Capacitance on IRQ/FT, RST, and DQ pins	C _{IO}			10	pF	1

AC TEST CONDITIONS

Output Load: 100 pF + 1TTL Gate
Input Pulse Levels: 0.0 to 3.0 Volts
Timing Measurement Reference Levels:

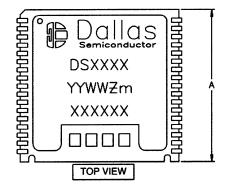
Input: 1.5V Output: 1.5V

Input Pulse Rise and Fall Times: 5 ns

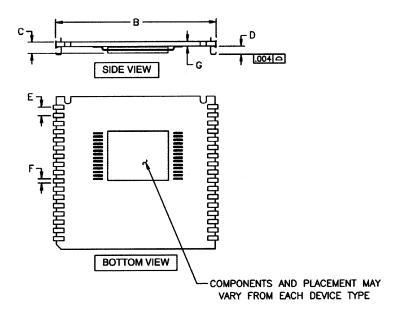
NOTES:

- 1. Voltage referenced to ground.
- 1. Typical values are at 25°C and nominal supplies.
- 3. Outputs are open.
- 4. Battery switch over occurs at the lower of either the battery voltage or V_{PF}.
- 5. The IRQ/FT and RST outputs are open drain.
- 6. Data retention time is at 25°C.
- 7. Dallas Semiconductor recommends that PowerCap Module bases experience one pass through solder reflow oriented with the label side up ("live-bug").
- 8. Hand soldering and touch-up: Do not touch or apply the soldering iron to leads for more than 3 seconds. To solder, apply flux to the pad, heat the lead frame pad and apply solder. To remove the part, apply flux, heat the lead frame pad until the solder reflow and use a solder wick to remove solder.
- 9. t_{AH1} , t_{DH1} are measured from \overline{WE} going high.
- 10. t_{AH2} , t_{DH2} are measured from \overline{CE} going high.

DS1557P



PKG	INCHES			
DIM	MIN	NOM	MAX	
A	0.920	0.925	0.930	
В	0.980	0.985	0.990	
C	-	-	0.080	
D	0.052	0.055	0.058	
${f E}$	0.048	0.050	0.052	
F	0.015	0.020	0.025	
G	0.025	0.027	0.030	

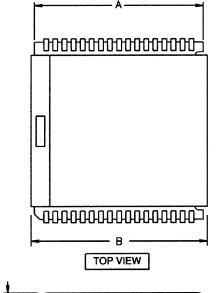


NOTE:

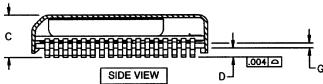
Dallas Semiconductor recommends that PowerCap Module bases experience one pass through solder reflow oriented with the label side up ("live-bug").

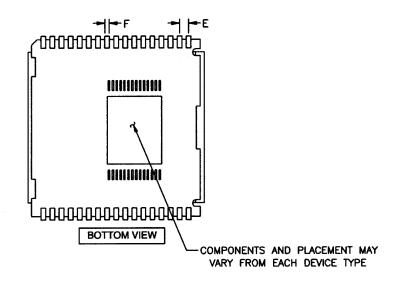
Hand Soldering and touch-up: Do not touch or apply the soldering iron to leads for more than 3 seconds. To solder, apply flux to the pad, heat the lead frame pad and apply solder. To remove the part, apply flux, heat the lead frame pad until the solder reflows and use a solder wick to remove solder.

DS1557P WITH DS9034PCX ATTACHED

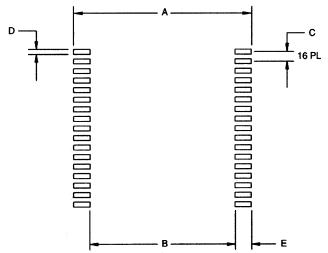


PKG	INCHES			
DIM	MIN	NOM	MAX	
A	0.920	0.925	0.930	
В	0.955	0.960	0.965	
C	0.240	0.245	0.250	
D	0.052	0.055	0.058	
E	0.048	0.050	0.052	
F	0.015	0.020	0.025	
G	0.020	0.025	0.030	





RECOMMENDED POWERCAP MODULE LAND PATTERN



PKG	INCHES			
DIM	MIN	NOM	MAX	
A	-	1.050	-	
В	-	0.826	-	
C	-	0.050	-	
D	-	0.030	-	
E	-	0.112	-	